

RQJ0202VGDQA

Silicon P Channel MOS FET
Power Switching

REJ03G1318-0300

Rev.3.00

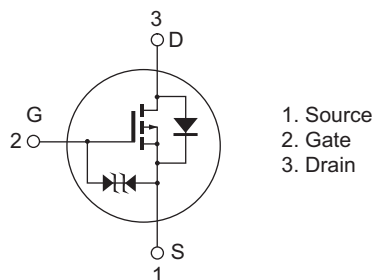
May 24, 2006

Features

- Low on-resistance
 $R_{DS(on)} = 83 \text{ m}\Omega$ typ ($V_{GS} = -4.5 \text{ V}$, $I_D = -1.4 \text{ A}$)
- Low drive current
- High speed switching
- 2.5 V gate drive

Outline

RENESAS Package code: PLSP0003ZB-A
(Package name: MPAK)



Note: Marking is "VG".

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-20	V
Gate to source voltage	V_{GSS}	+8 / -12	V
Drain current	I_D	-2.7	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-8.0	A
Body - drain diode reverse drain current	I_{DR}	-2.7	A
Channel dissipation	P_{ch} ^{Note2}	0.8	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes: 1. $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$

2. When using the glass epoxy board (FR-4: 40 x 40 x 1 mm)

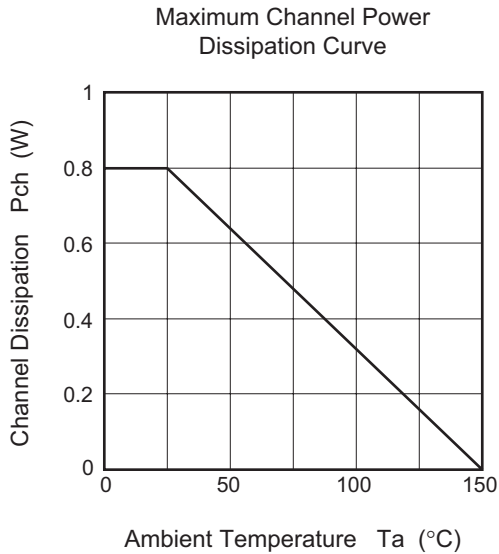
Electrical Characteristics

(Ta = 25°C)

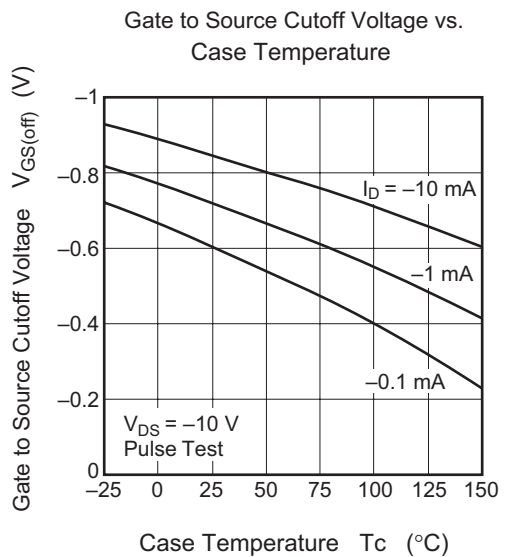
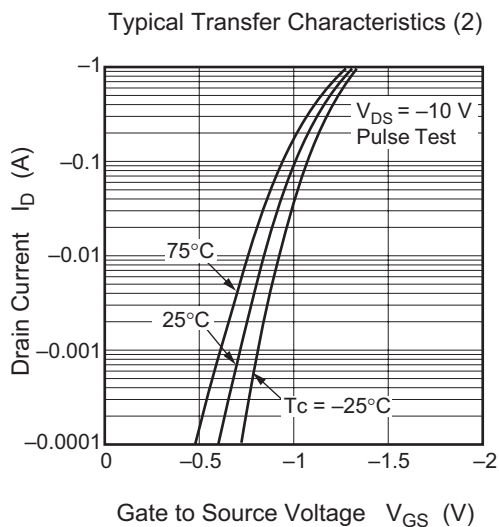
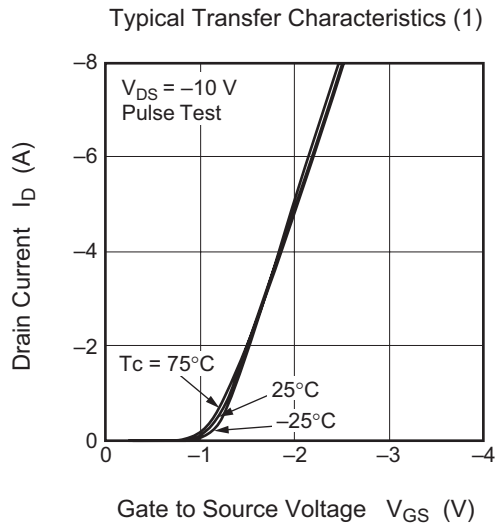
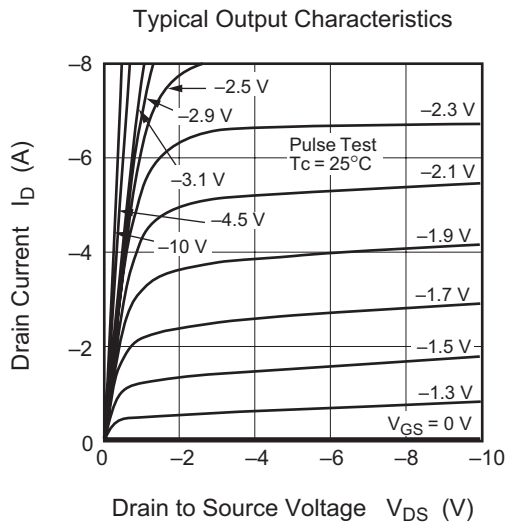
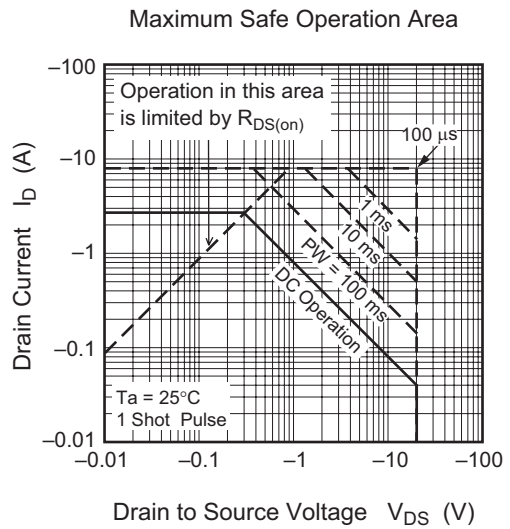
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-20	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	+8	—	—	V	$I_G = +100 \text{ } \mu\text{A}$, $V_{DS} = 0$
	$V_{(BR)GSS}$	-12	—	—	V	$I_G = -100 \text{ } \mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	+10	μA	$V_{GS} = +6 \text{ V}$, $V_{DS} = 0$
	I_{GSS}	—	—	-10	μA	$V_{GS} = -10 \text{ V}$, $V_{DS} = 0$
Drain to source leak current	I_{DSS}	—	—	-1	μA	$V_{DS} = -20 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.4	—	-1.4	V	$V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$
Drain to source on state resistance	$R_{DS(on)}$	—	83	105	m Ω	$I_D = -1.4 \text{ A}$, $V_{GS} = -4.5 \text{ V}^{\text{Note3}}$
	$R_{DS(on)}$	—	124	170	m Ω	$I_D = -1.4 \text{ A}$, $V_{GS} = -2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	$ y_{fs} $	3	4.5	—	S	$I_D = -1.4 \text{ A}$, $V_{DS} = -10 \text{ V}^{\text{Note3}}$
Input capacitance	C_{iss}	—	365	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	C_{oss}	—	102	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	70	—	pF	$f = 1 \text{ MHz}$
Turn - on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = -1.4 \text{ A}$
Rise time	t_r	—	57	—	ns	$V_{GS} = -4.5 \text{ V}$
Turn - off delay time	$t_{d(off)}$	—	40	—	ns	$R_L = 7.1 \text{ } \Omega$
Fall time	t_f	—	21	—	ns	$R_g = 4.7 \text{ } \Omega$
Total gate charge	Q_g	—	4.3	—	nC	$V_{DD} = -10 \text{ V}$
Gate to source charge	Q_{gs}	—	0.6	—	nC	$V_{GS} = -4.5 \text{ V}$
Gate to drain charge	Q_{gd}	—	1.7	—	nC	$I_D = -2.7 \text{ A}$
Body - drain diode forward voltage	V_{DF}	—	-0.85	-1.1	V	$I_F = -2.7 \text{ A}$, $V_{GS} = 0^{\text{Note3}}$

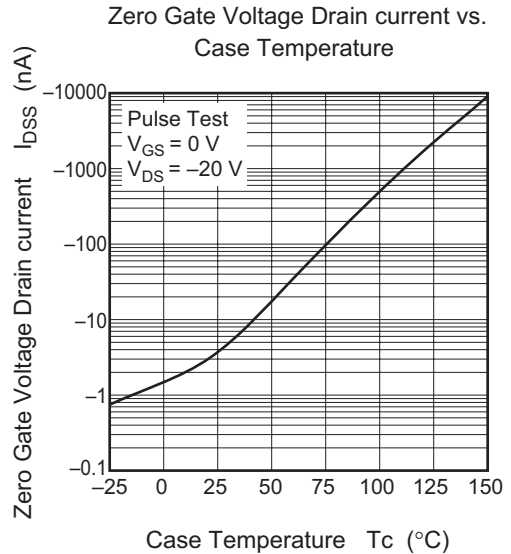
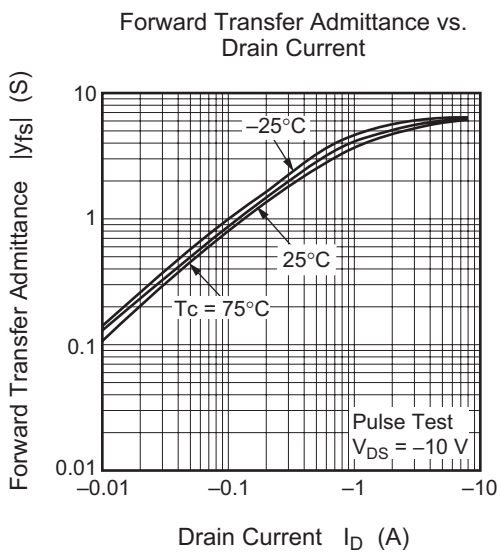
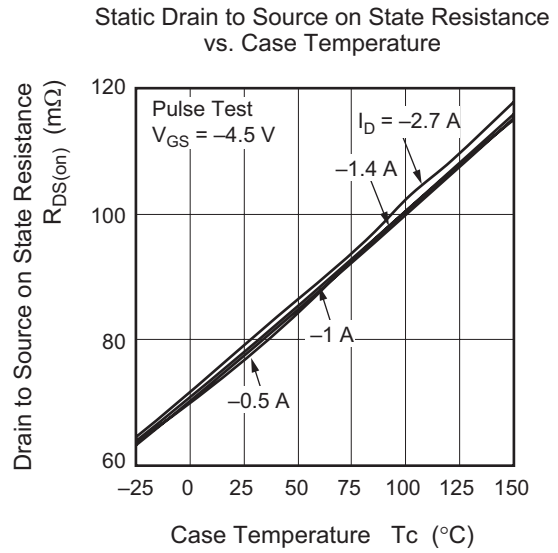
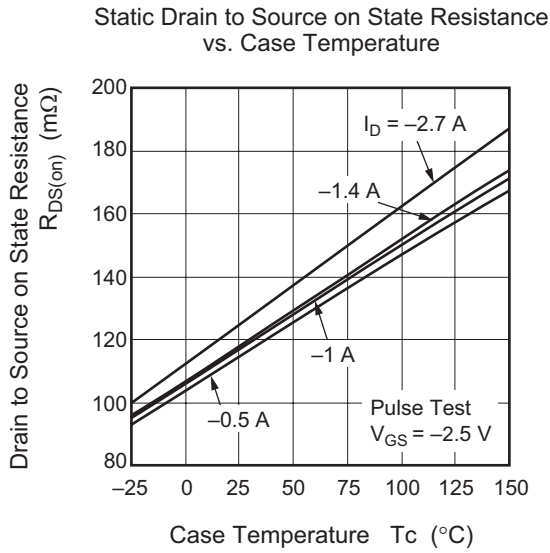
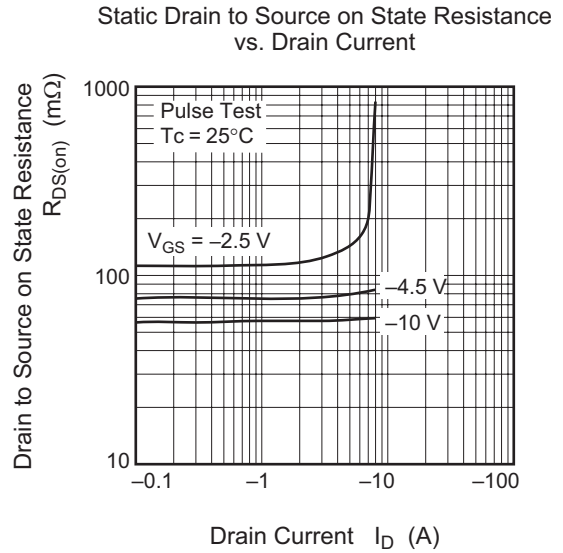
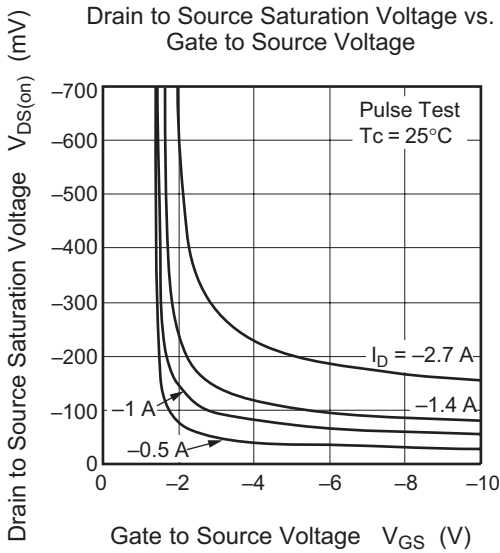
Notes: 3. Pulse test

Main Characteristics

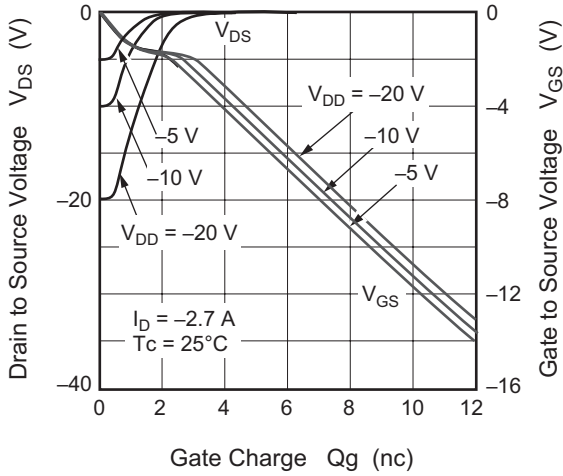


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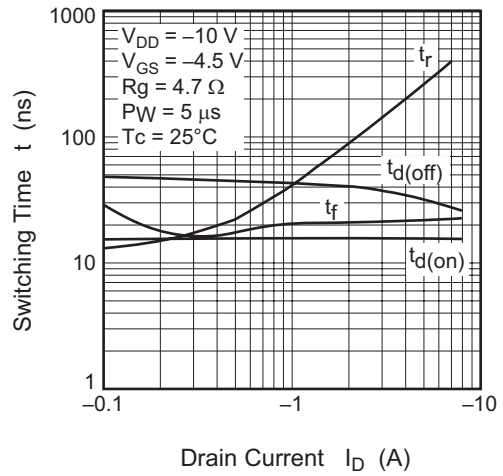




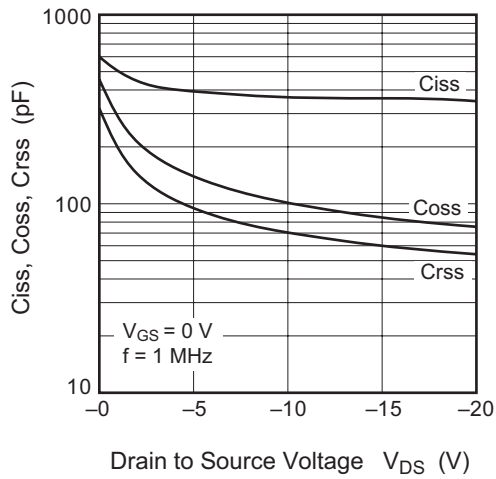
Dynamic Input Characteristics



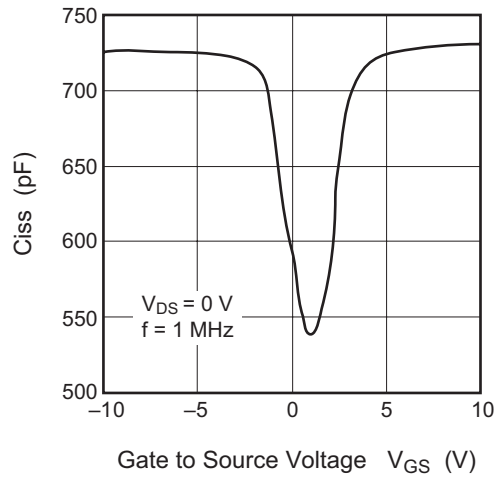
Switching Characteristics



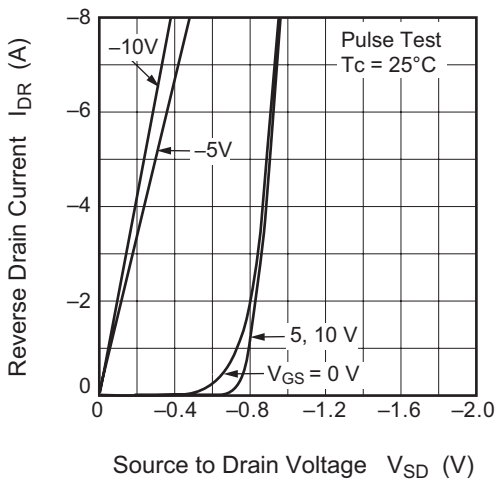
Typical Capacitance vs. Drain to Source Voltage



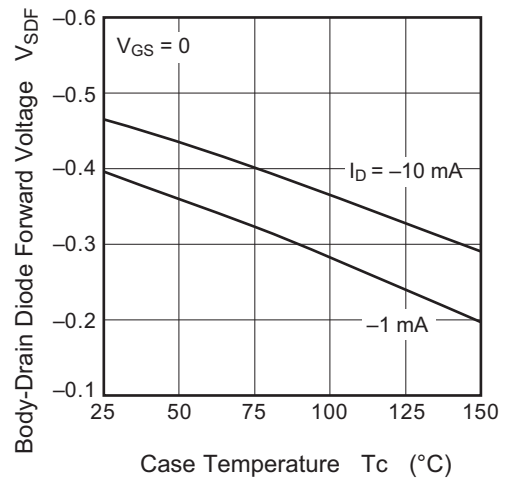
Input Capacitance vs. Gate to Source Voltage



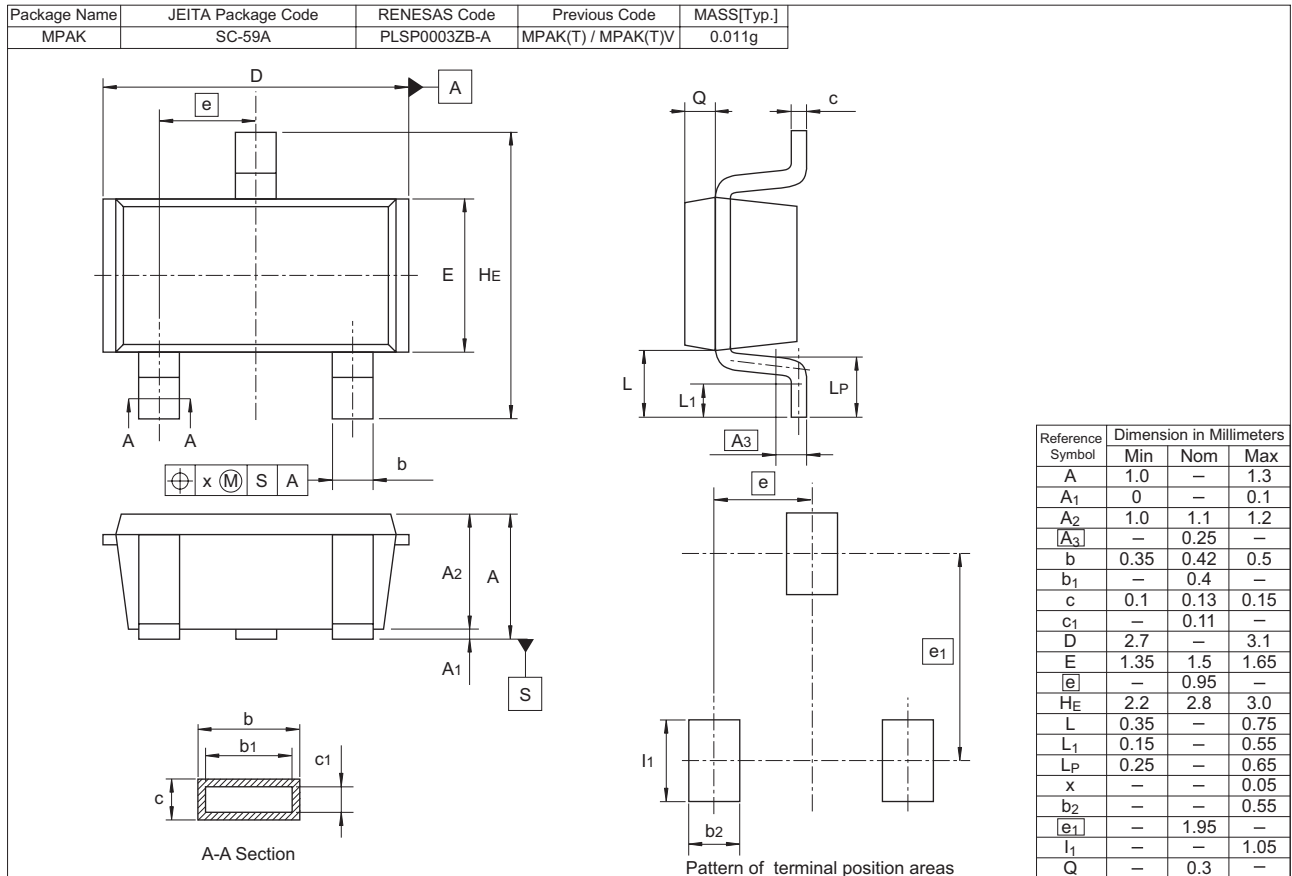
Reverse Drain Current vs. Source to Drain Voltage



Body-Drain Diode Forward Voltage vs. Case Temperature



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
RQJ0202VGDQATL-E	3000 pcs.	φ178 mm reel, 8 mm Emboss taping

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